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Notice of Allowability	Application No.	Applicant(s)	
	10/624,817	GEALY ET AL.	
	Examiner	Art Unit	
	Pamela E. Perkins	2822	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. ☒ This communication is responsive to the amendment filed on 16 December 2004.
2. ☒ The allowed claim(s) is/are 1-20.
3. ☒ The drawings filed on 22 July 2002 are accepted by the Examiner.
4. ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) ☐ All b) ☐ Some* c) ☐ None of the:
 1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

* Certified copies not received: _____.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.
THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

5. ☐ A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
 6. ☐ CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
 - (a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 - 1) ☐ hereto or 2) ☐ to Paper No./Mail Date _____.
 - (b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date _____.
- Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).
7. ☐ DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

- | | |
|---|---|
| 1. <input type="checkbox"/> Notice of References Cited (PTO-892) | 5. <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 2. <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 6. <input type="checkbox"/> Interview Summary (PTO-413),
Paper No./Mail Date _____ |
| 3. <input type="checkbox"/> Information Disclosure Statements (PTO-1449 or PTO/SB/08),
Paper No./Mail Date _____ | 7. <input type="checkbox"/> Examiner's Amendment/Comment |
| 4. <input type="checkbox"/> Examiner's Comment Regarding Requirement for Deposit
of Biological Material | 8. <input checked="" type="checkbox"/> Examiner's Statement of Reasons for Allowance |
| | 9. <input type="checkbox"/> Other _____ |

[Handwritten signature and stamp]

DETAILED ACTION

This office action is in response to the filing of the amendment on 16 December 2004. Claims 1-20 are pending.

Allowable Subject Matter

Claims 1-20 are allowed.

Reasons for Allowance

The following is an examiner's statement of reasons for allowance: prior art does not anticipate, teach, or suggest a method for oxidizing one of a gate dielectric layer and a cell dielectric layer on a portion of a silicon substrate in an atmosphere where the temperature of the silicon substrate is raised to a temperature of at least about 600°C; providing a gas atmosphere of N₂O, the gas atmosphere of N₂O having a pressure of at least about five atmospheres for contacting at least a portion of the silicon substrate using a catalytically disassociated gas atmosphere of N₂O; and contacting a portion of the gas atmosphere of N₂O with a catalytic matrix consisting of one or more metals for forming a catalytically disassociated gas atmosphere of N₂O for contacting at least a portion of the silicon substrate.

For example, Yamazaki et al. (5,840,600) disclose a method for oxidizing one of a gate dielectric layer and a cell dielectric layer on a portion of a silicon substrate in an atmosphere where the temperature of the silicon substrate is raised to a temperature in a range of about 500°C to 700°C; providing a gas atmosphere of N₂O, the gas atmosphere of N₂O having a pressure of at least about five atmospheres for contacting at least a portion of the silicon substrate; and contacting a portion of the gas

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atmosphere of N_2O in a catalytic reaction. However, Yamazaki et al. do not disclose, anticipate, teach, or suggest contacting a portion of the gas atmosphere of N_2O with a catalytic matrix consisting of one or more metals for forming a catalytically disassociated gas atmosphere of N_2O for contacting at least a portion of the silicon substrate.

Kamiyama (5,508,221) discloses a method for oxidizing of a portion of a silicon substrate where the temperature of the silicon substrate is raised to a temperature in a range of about $700^{\circ}C$ to about $850^{\circ}C$; providing a gas atmosphere of N_2O . However, Kamiyama does not disclose, anticipate, teach or suggest contacting a portion of the gas atmosphere of N_2O with a catalytic matrix consisting of one or more metals for forming a catalytically disassociated gas atmosphere of N_2O for contacting at least a portion of the silicon substrate.

The prior art made of record in this action does not anticipate, teach, or suggest a method for oxidizing one of a gate dielectric layer and a cell dielectric layer on a portion of a silicon substrate in an atmosphere where the temperature of the silicon substrate is raised to a temperature of at least about $600^{\circ}C$; providing a gas atmosphere of N_2O , the gas atmosphere of N_2O having a pressure of at least about five atmospheres for contacting at least a portion of the silicon substrate using a catalytically disassociated gas atmosphere of N_2O ; and contacting a portion of the gas atmosphere of N_2O with a catalytic matrix consisting of one or more metals for forming a catalytically disassociated gas atmosphere of N_2O for contacting at least a portion of the silicon substrate.

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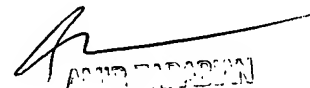
Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Pamela E. Perkins whose telephone number is (571) 272-1840. The examiner can normally be reached on Monday thru Friday, 9:00am to 5:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).


AMIR ZARABIAN
SUPERVISOR
ART UNIT 2822

PEP